

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 24, line 22, as follows:

[[FIG. 2]] FIGS. 2(a) and (b) illustrate ~~illustrates~~ a relationship between a tip portion of an ejection tube in the microsphere arranging apparatus and a semiconductor device mounted on a mount base.

Please amend the paragraph beginning at page 24, line 25, as follows:

[[FIG. 3]] FIGS. 3(a) and (b) show ~~[[shows]]~~ the composition of a pump of the microsphere arranging apparatus.

Please amend the paragraph beginning at page 25, line 7, as follows:

~~FIG. 7 is a~~ FIGS. 7(a), (b) and (c) are plain views showing a relief groove formed in connection with the resist hole.

Please amend the paragraph beginning at page 25, line 13, as follows:

~~FIG. 10 illustrates~~ FIGS. 10(a) and (b) illustrate a situation that a semiconductor device is mounted on a rotary mounting unit of the microsphere arranging apparatus.

Please amend the paragraph beginning at page 26, line 6, as follows:

~~FIG. 18 is a~~ FIGS. 18(a) and (b) are plain views showing a relief groove formed in connection with a resist hole.

Please amend the paragraph beginning at page 26, line 8, as follows:

~~FIG. 19 is a~~ FIGS. 19(a), (b) and (c) are plain views showing the shape of resist holes and a relief groove formed in connection with a resist hole.

Please amend the paragraph beginning at page 26, line 20, as follows:

~~FIG. 24 is a~~ FIGS. 24(a), (b) and (c) are cross sectional views showing a relief groove formed in the mask.

Please amend the paragraph beginning at page 62, line 5, as follows:

Referring to FIGS. 18(a), (b) and (c), 19(a), (b) and (c), 20 and 21, various shapes of resist hole will be detailed.

Please amend the paragraph beginning at page 62, line 7, as follows:

FIGS. 18(a), (b) and (c) and 19(a), (b) and (c) are plain views showing the shapes of a penetrating hole to mount the microsphere formed in the resist of semiconductor device in the seventh embodiment of the invention. FIG. 21 is a cross sectional view showing a penetrating hole to mount the microsphere formed in the resist of semiconductor device in the seventh embodiment of the invention.

Please amend the paragraph beginning at page 67, line 9, as follows:

~~FIG. 24 is a~~ FIGS. 24(a), (b) and (c) are cross sectional views showing a relief groove formed in the mask. As shown, the relief groove 49 is formed on only the semiconductor wafer 43 side without penetrating the mask 46, and thereby the gas or liquid can be removed easily. The mask 46 thus structured may be formed by conducting the electroforming of two or more stages. Further, it may be formed by half-etching, laser processing or mechanical processing after a mask is made by the abovementioned method.